

7. (Amended) A method of forming a polycrystalline silicon layer, comprising:

forming an amorphous silicon layer on a substrate;

melting said amorphous silicon layer using a laser beam so as to form a polycrystalline silicon layer; and

re-melting an upper portion of said polycrystalline silicon layer using a laser beam so as to re-crystallize said upper portion,

wherein at least some of said re-melting of said upper portion of said polycrystalline silicon layer is performed as said amorphous silicon layer is melted.

Please **ADD** new claims 18 and 19.

18. A method of forming a polycrystalline silicon layer, comprising:

forming an amorphous silicon layer on a substrate;

melting the amorphous silicon layer using a laser beam thereby forming the polycrystalline silicon layer by adopting a mask; and

melting an upper portion of the polycrystalline silicon layer using the laser beam by adopting the mask thereby recrystallizing the upper portion of the polycrystalline silicon layer,

wherein said melted amorphous silicon layer and said polycrystalline silicon layer of which upper portion is melted exist at the same time during at least a certain time period of the formation of the polycrystalline silicon layer.